

4.4A, 700V N-CHANNEL POWER MOSFET

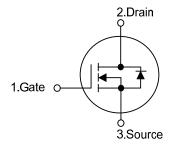
DESCRIPTION

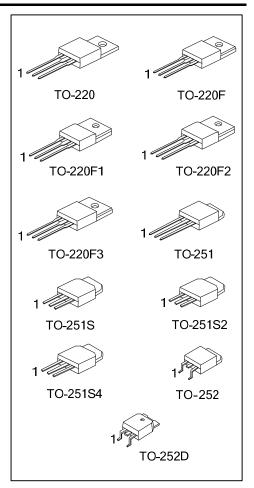
The UTC **4N70K-MT** is a high voltage power MOSFET and is designed to have better characteristics, such as fast switching time, low gate charge, low on-state resistance and high rugged avalanche. This high speed switching power MOSFET is usually used in power supplies, PWM motor controls, high efficient DC to DC converters and bridge circuits.

FEATURES

- * $R_{DS(ON)}$ < 3.2 Ω @ V_{GS} = 10 V, I_D = 2.2 A
- * Fast Switching Capability
- * Avalanche Energy Specified
- * Improved dv/dt Capability, High Ruggedness

SYMBOL

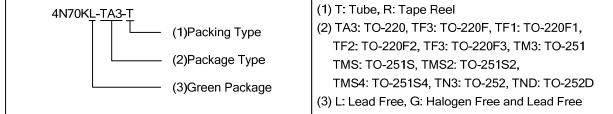




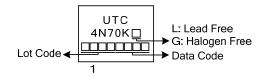
Power MOSFET

ORDERING INFORMATION

| Ordering Number | | Daakaga | Pin | Decking | | | |
|-----------------------------|-----------------------|----------|-------------|---------|---|-----------|--|
| Lead Free | Halogen Free | Package | 1 | 2 | 3 | Packing | |
| 4N70KL-TA3-T | 4N70KG-TA3-T | TO-220 | O-220 G D S | | S | Tube | |
| 4N70KL-TF3-T | 4N70KG-TF3-T | TO-220F | G | D | S | Tube | |
| 4N70KL-TF1-T | 4N70KG-TF1-T | TO-220F1 | G | D | S | Tube | |
| 4N70KL-TF2-T | 4N70KG-TF2-T | TO-220F2 | G | D | S | Tube | |
| 4N70KL-TF3-T | 4N70KG-TF3-T | TO-220F3 | G | D | S | Tube | |
| 4N70KL-TM3-T | 4N70KG-TM3-T | TO-251 | G | D | S | Tube | |
| 4N70KL-TMS-T | 4N70KG-TMS-T | TO-251S | G | D | S | Tube | |
| 4N70KL-TMS2-T | 4N70KG-TMS2-T | TO-251S2 | G | D | S | Tube | |
| 4N70KL-TMS4-T | 4N70KG-TMS4-T | TO-251S4 | G | D | S | Tube | |
| 4N70KL-TN3-R | 4N70KG-TN3-R | TO-252 | G | D | S | Tape Reel | |
| 4N70KL-TND-R | 4N70KG-TND-R | TO-252D | G | D | S | Tape Reel | |
| Note: Pin Assignment: G: Ga | te D: Drain S: Source | | | | | | |



MARKING





| PARAMETER | | SYMBOL | RATINGS | UNIT |
|------------------------------------|---|------------------|------------|------|
| Drain-Source Voltage | | V _{DSS} | 700 | V |
| Gate-Source Voltage | | V _{GSS} | ±30 | V |
| Drain Current | Continuous | I _D | 4.4 | А |
| | Pulsed (Note 2) | I _{DM} | 17.6 | А |
| Avalanche Energy | Single Pulsed (Note 3) | E _{AS} | 180 | mJ |
| Power Dissipation | TO-220 | | 106 | W |
| | TO-220F/TO-220F1 TO-220F2/TO-220F3 | P | 36 | W |
| | TO-251/TO-251S TO-251S2/TO-251S4 TO-252/TO-252D | P _D | 49 | w |
| Peak Diode Recovery dv/dt (Note 4) | | dv/dt | 4.5 | V/ns |
| Junction Temperature | | TJ | +150 | °C |
| Operating Temperature | | T _{OPR} | -55 ~ +150 | °C |
| Storage Temperature | | T _{STG} | -55 ~ +150 | °C |

■ ABSOLUTE MAXIMUM RATINGS (T_A = 25°C, unless otherwise specified)

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

2. Repetitive Rating : Pulse width limited by maximum junction temperature

3. L = 22.5mH, I_{AS} = 4 A, V_{DD} = 50V, R_{G} = 25 $\Omega,$ Starting T_{J} = 25°C

4. $I_{SD} \le 4.4A$, di/dt $\le 200A/\mu s$, $V_{DD} \le BV_{DSS}$, Starting $T_J = 25^{\circ}C$

THERMAL DATA

| PARAMETER | | SYMBOL | RATINGS | UNIT |
|---------------------|---|-----------------|---------|------|
| Junction to Ambient | TO-220/TO-220F TO-220F1/TO-220F2 TO-220F3 | 0 | 62.5 | °C/W |
| | TO-251/TO-251S TO-251S2/TO-251S4 TO-252/TO-252D | θ _{JA} | 110 | °C/W |
| Junction to Case | TO-220 | | 1.18 | °C/W |
| | TO-220F/TO-220F1 TO-220F3 | | 3.47 | °C/W |
| | TO-220F2 | θ _{JC} | 3.4 | °C/W |
| | TO-251/TO-251S TO-251S2/TO-251S4 TO-252/TO-252D | | 2.55 | °C/W |



| | | , | | 1 | r | r | |
|--|-------------------|--------------------------------------|---|-----|-----|------|------|
| PARAMETER | | SYMBOL | TEST CONDITIONS | MIN | TYP | MAX | UNIT |
| OFF CHARACTERISTICS | | | | | | | |
| Drain-Source Breakdown Voltage | | BV _{DSS} | V _{GS} = 0 V, I _D = 250 μA | 700 | | | V |
| Drain-Source Leakage Current | | I _{DSS} | V _{DS} = 700 V, V _{GS} = 0 V | | | 10 | μA |
| Gate-Source Leakage Current | Forward | | V_{GS} = 30 V, V_{DS} = 0 V | | | 100 | nA |
| | Reverse | I _{GSS} | V_{GS} = -30 V, V_{DS} = 0 V | | | -100 | ПА |
| Breakdown Voltage Temperature | Coefficient | $\triangle BV_{DSS} / \triangle T_J$ | $I_D = 250 \mu A$, Referenced to $25^{\circ}C$ | | 0.6 | | V/°C |
| ON CHARACTERISTICS | | | | | | | |
| Gate Threshold Voltage | | V _{GS(TH)} | V _{DS} = V _{GS} , I _D = 250 μA | 2.0 | | 4.0 | V |
| Static Drain-Source On-State Resistance | | R _{DS(ON)} | V _{GS} = 10 V, I _D = 2.2 A | | | 3.2 | Ω |
| DYNAMIC CHARACTERISTICS | | | | | | | |
| Input Capacitance | put Capacitance | | | | 350 | 550 | pF |
| Output Capacitance Reverse Transfer Capacitance | | Coss | V _{DS} = 25 V, V _{GS} = 0 V, f = 1MHz | | 55 | 85 | pF |
| | | C _{RSS} | | | 5 | 10 | pF |
| SWITCHING CHARACTERISTICS | 5 | | | | | | |
| Turn-On Delay Time | ırn-On Delay Time | | | | 50 | 70 | ns |
| Turn-On Rise Time | | t _{D(ON)} t _R | $V_{DD} = 30V, I_D = 0.5A,$ | | 40 | 60 | ns |
| Turn-Off Delay Time | | t _{D(OFF)} | R _G = 25Ω (Note 1, 2) | | 75 | 90 | ns |
| Turn-Off Fall Time | -Off Fall Time | | | | 30 | 45 | ns |
| Total Gate Charge | | Q _G | V _{DS} = 50V, I _D = 1.3A, | | 14 | | nC |
| Gate-Source Charge | | Q _{GS} | V _{DS} = 50V, I _D = 1.3A, V _{GS} = 10 V (Note 1, 2) | | 5 | | nC |
| Gate-Drain Charge | e-Drain Charge | | v_{GS} 10 V (Note 1, 2) | | 2.5 | | nC |
| SOURCE- DRAIN DIODE RATING | GS AND CI | HARACTERIS | TICS | | | _ | |
| Drain-Source Diode Forward Voltage | | V _{SD} | $V_{GS} = 0 V, I_{S} = 4.4 A$ | | | 1.4 | V |
| Maximum Continuous Drain-Sourc | e Diode | | | | | 4.4 | ٨ |
| Forward Current | | Is | | | | 4.4 | A |
| Maximum Pulsed Drain-Source Diode | | | | | | 16 | А |
| Forward Current | | I _{SM} | | | | 10 | A |

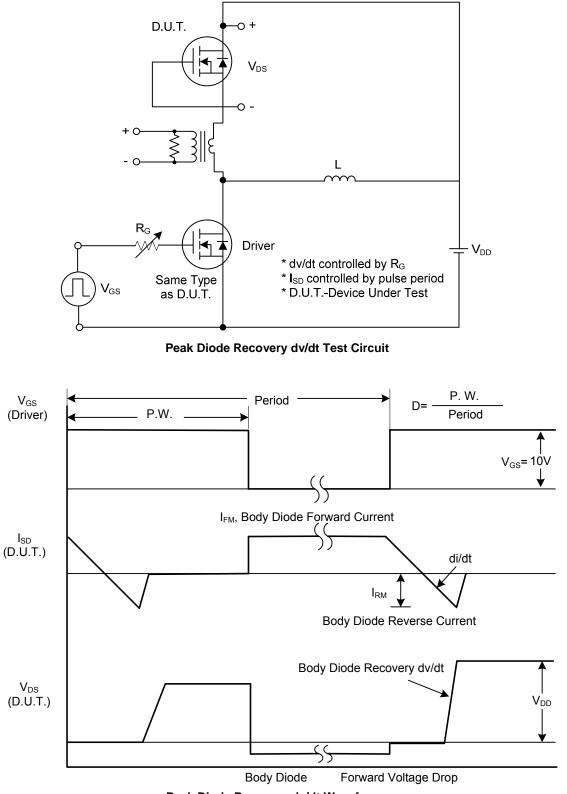
■ ELECTRICAL CHARACTERISTICS (T_A =25°C, unless otherwise specified)

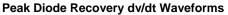
Notes: 1. Pulse Test: Pulse width \leq 300µs, Duty cycle \leq 2%

2. Essentially independent of operating temperature



TEST CIRCUITS AND WAVEFORMS

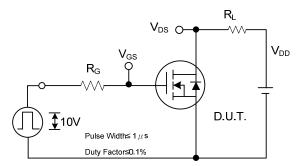




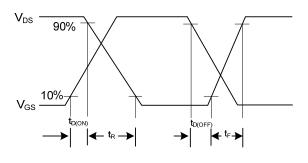


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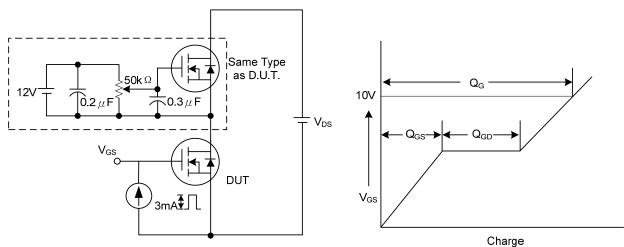
■ TEST CIRCUITS AND WAVEFORMS (Cont.)



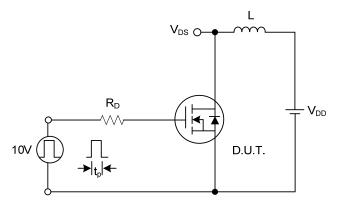
Switching Test Circuit



Switching Waveforms

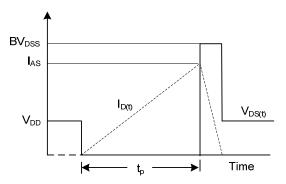


Gate Charge Test Circuit



Unclamped Inductive Switching Test Circuit

Gate Charge Waveform

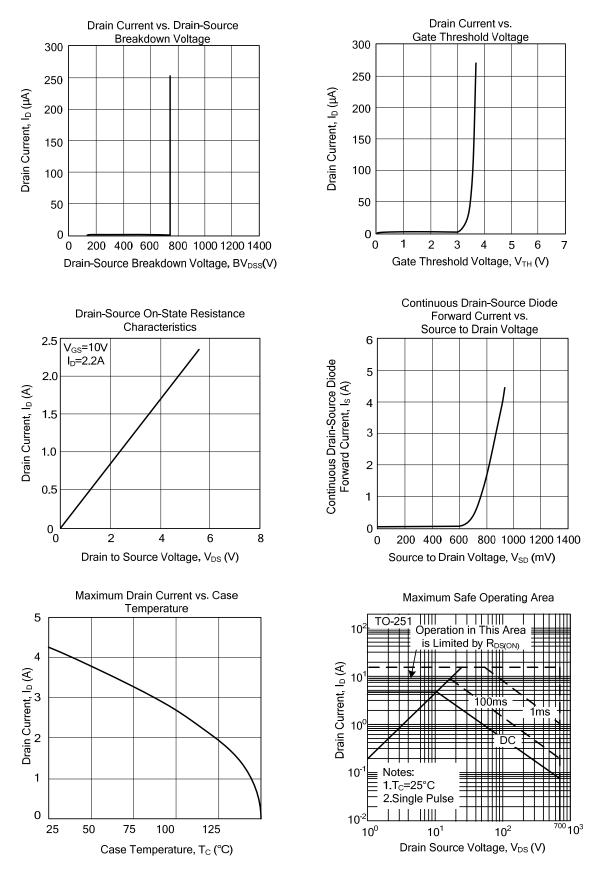


Unclamped Inductive Switching Waveforms



Power MOSFET

TYPICAL CHARACTERISTICS





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